

resist-etching step, both end portions of the resist in the channel direction are removed by means of ashing with the use of a gas containing at least one of O₂ and ozone.

39. (Amended) The method of fabricating an LDD thin film transistor in accordance with claim 37, wherein a thermal oxide film as the reaction product film is formed by oxidizing the gate electrode material metal with heat.

43. (Amended) The method of fabricating an LDD thin film transistor in accordance with claim 41, wherein the gate electrode is made of an Mo-W alloy having Mo content of 15-50 atom%.

~~Please add the following new claims:~~

53. (New) The method for fabricating an LDD thin film transistor in accordance with claim 2, wherein, in the isolated resist-etching step, both end portions of the resist in the channel direction are removed by means of ashing with the use of a gas containing at least one of O₂ and ozone.

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54. (New) The method of fabricating an LDD thin film transistor in accordance with claim 38, wherein a thermal oxide film as the reaction product film is formed by oxidizing the gate electrode material metal with heat.
